

ABSTRACT OF THE DISCLOSURE

The semiconductor laser device has the lower clad layer, active layer, upper clad layer, contact layer, the insulating film, and the positive electrode sequentially formed on the semiconductor substrate. The upper clad layer, the contact layer and the insulating film form the ridge. The positive electrode covers the upper and side
5 faces of the ridge. The thickness of the positive electrode on the upper and side faces of the ridge is preferably substantially the same and it is not less than 150 nm.

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